

EMD1705QFN4 Driver Amplifier

DC-20 GHz GaAs PHEMT MMIC



Eclipse Microdevices EMD1705QFN4 is a GaAs MMIC PHEMT distributed general purpose driver amplifier. This MMIC is ideal for applications that requires a typical P1dB output power of +23 dBm up to 14 GHz, while requiring only 190mA from a + 8 Volt supply. Gain flatness of this device is less than 2.0 dB from DC to 20 GHz. The EMD1705QFN4 comes in a small RoHS compliant 4mm QFN leadless package and has excellent RF and thermal properties, ideal for commercial and industrial applications.

Technical Characteristics

Product Features

15.0 dB gain @ 10 GHz
+24.0 dBm P1dB output power @ 10 GHz
+8.0V @ 190 mA typical supply voltage
Low cost QFN 4mm leadless RoHS compliant/hermetically sealed
Die available upon request

Max. Ratings

RF Input Power:	+18.0 dBm
Drain Voltage (Vdd):	+8.0 VDC
Gate Voltage (Vgg):	-2.0 to 0 VDC
Max. T _j 85° C:	+110°C
Storage Temperature:	-55 to +150°
Operating Temperature:	-40 to +85°

Electrical Specifications @ +25°C, Vdd= 8.0, Ids= 190mA

Parameters	Freq. (GHz)	Min.	Typical	Max.	Units
Gain	2.0		16.7		dB
	8.0		15.5		dB
	14.0		17.5		dB
	20.0		15.3		dB
Gain Flatness	DC to 10.0 GHz		+/- 1.00	+/- 1.40	dB
	10.0 to 20 GHz		+/- 1.45	+/- 1.80	dB
Gain Variation Over Temperature				.02	dB/°C
Noise Figure			6.5		dB
Input Return Loss			10.0		dB
			10.0		dB
			10.0		dB
Output Return Loss	10.0		8.0		dB
			9.3		dB
			8.0		dB
1dB Compression Point	2.0		23.0		dBm
	8.0		24.0		dBm
	14.0		22.5		dBm
	20.0		19.1		dBm
Saturated Output Power	2.0		25.0		dBm
	8.0		24.6		dBm
	14.0		24.2		dBm
	20.0		21.0		dBm
3rd Order Intercept Point			28.0		dBm

About EclipseMDI

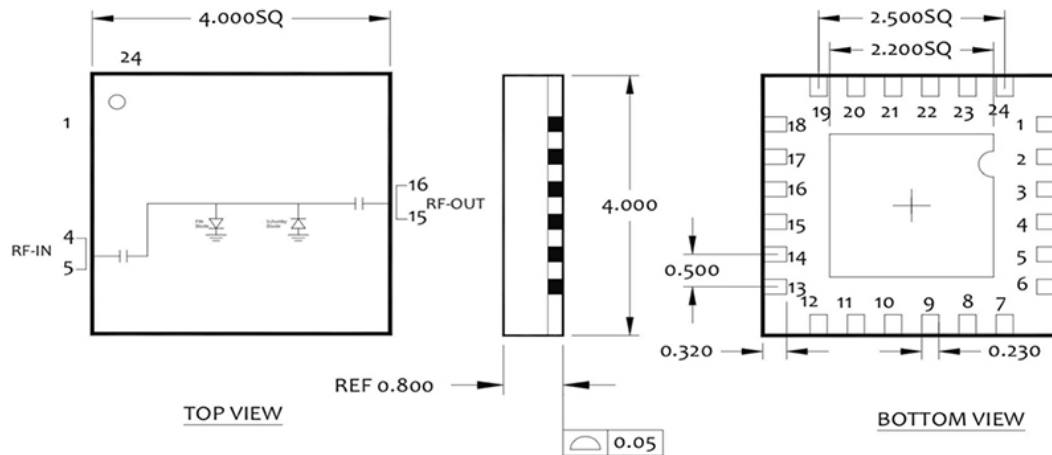
ECLIPSE MDI is located in San Jose, California. ECLIPSE has been developing high performance analog semiconductors for use in wireless radio frequency (RF), microwave, and millimeter wave for commercial and industrial applications. ECLIPSE has formed a strategic alliances - with foundries that feature leading state-of-the-art process technologies and with manufacturing facilities for high-volume production of innovative RFIC's.

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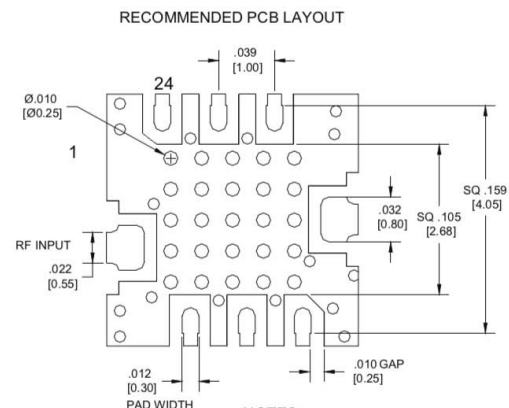
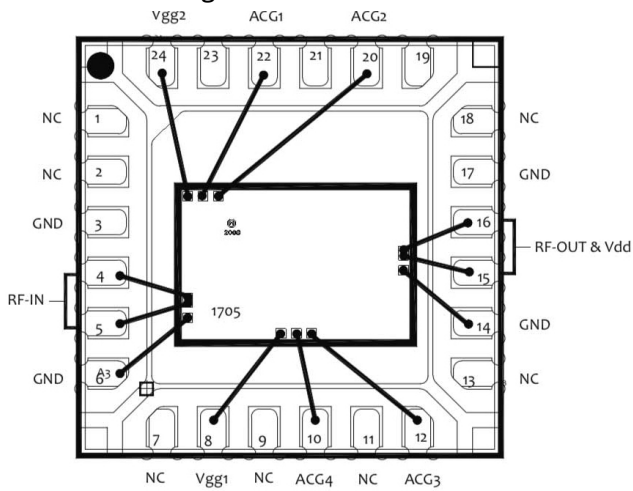


Outline Drawing



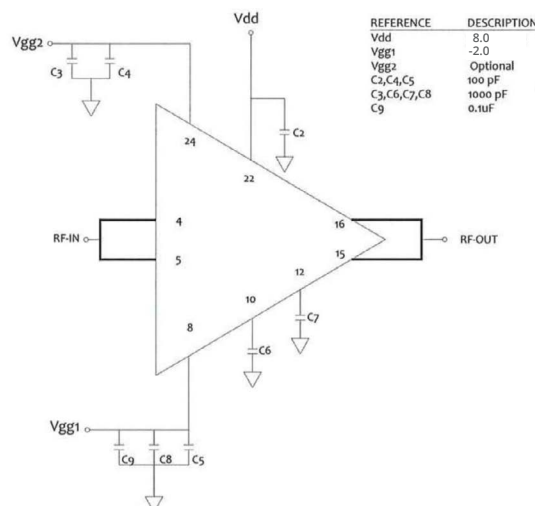
Functional block diagram

Recommended PCB layout



- NOTES:
 1. MATERIAL: ROGERS 4350, 10 MIL THICK
 2. DIMENSIONS ARE IN INCHES[MM]

Application Circuit



NOTE: Adjust Vgg1 to between -2 to 0 volts to achieve I_{ds}: 190mA typical